

N-channel TrenchMOS standard level FET Rev. 02 — 16 March 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. **Quick reference**

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sources									
Suitable	for	thor	mal	h.	do	m	andir	na	

Suitable for standard level gate drive

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

	Quick reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	$V_{GS} = 5 V; T_{mb} = 25 °C;$ see <u>Figure 1</u> and <u>3</u>	-	-	38	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	88	W
Avalance	he ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 34 \text{ A}; \text{V}_{sup} \leq 55 \text{ V}; \\ R_{GS} &= 50 \Omega; \text{V}_{GS} = 10 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	58	mJ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 44 \text{ V}; \text{ see } \frac{\text{Figure } 14}{100000000000000000000000000000000000$	-	9	-	nC
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{and } \underline{12}}$	-	26	30	mΩ



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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7230-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	55	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{2} \text{ and } \frac{3}{2}$		-	38	А
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>		-	27	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed}; \text{ see } \frac{\text{Figure 3}}{10 \mu\text{s}}$	[1]	-	150	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	88	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dr	ain diode					
I _S	source current	T _{mb} = 25 °C		-	38	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	150	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ I_D = 34 \text{ A}; \text{V}_{sup} \leq 55 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{V}_{GS} = 10 \text{ V}; \\ \text{T}_{j(\text{init})} = 25 ^\circ\text{C}; \text{ unclamped} $		-	58	mJ

[1] Peak drain current is limited by chip, not package.

BUK7230-55A

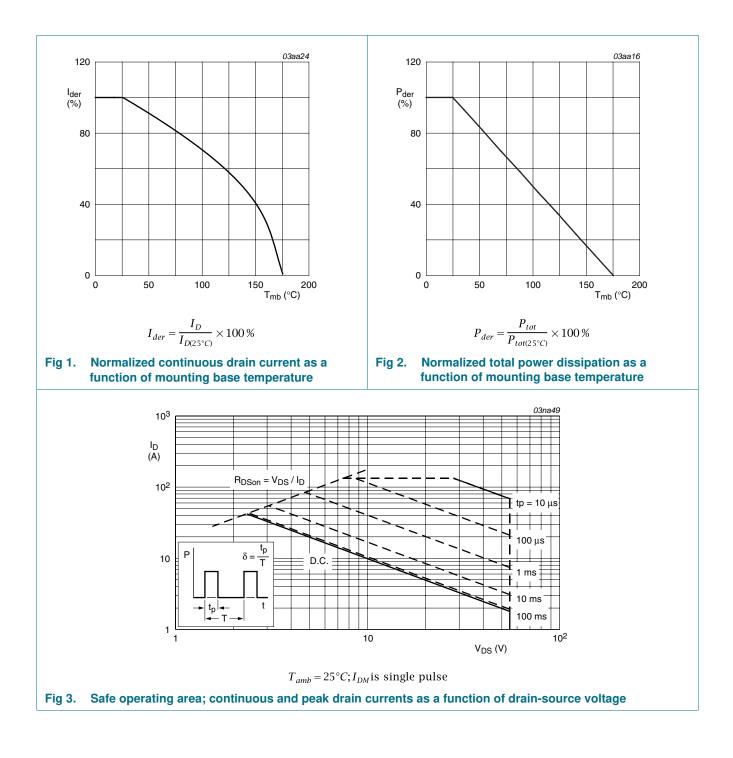


Table 5

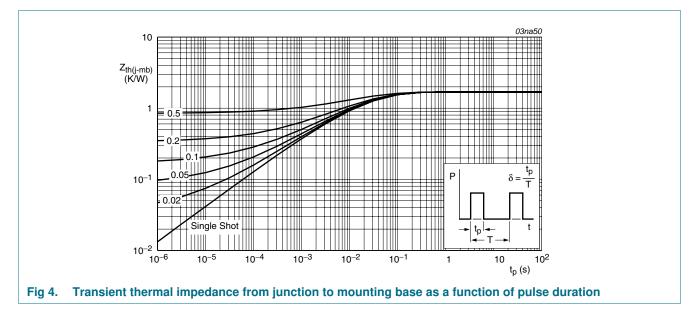
BUK7230-55A

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5. Thermal characteristics

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Table 5.	Inermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting bas	se	-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	see Figure 4	-	71.4	-	K/W

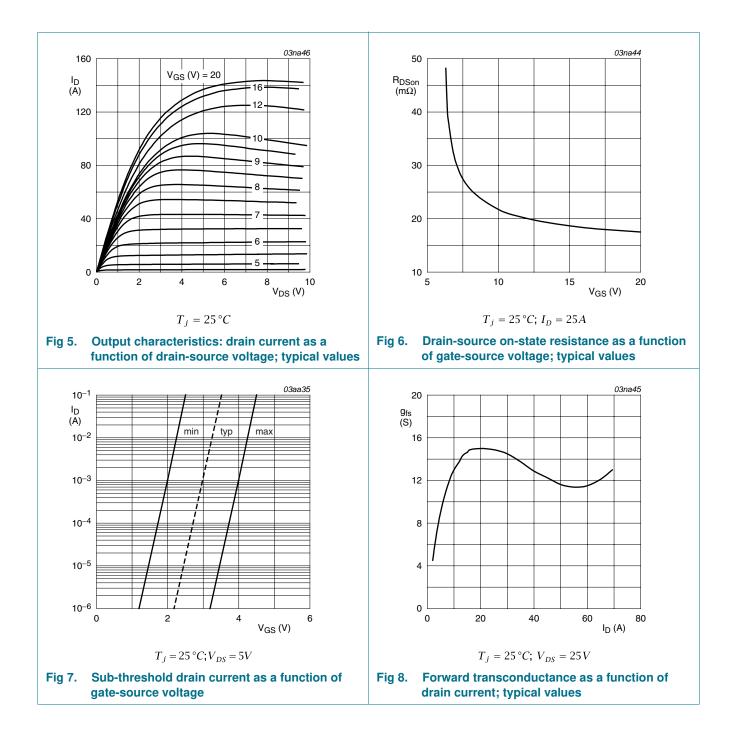


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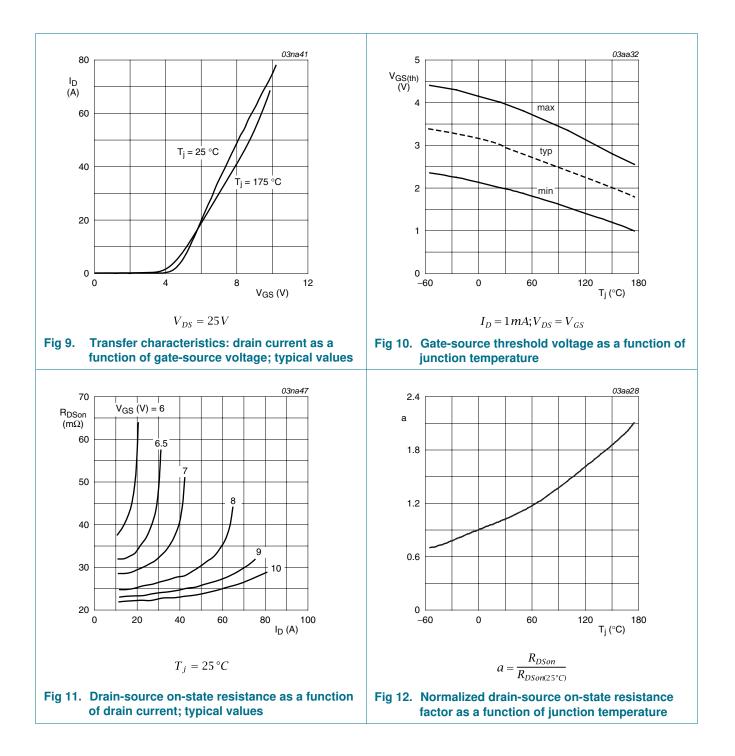
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
V _{GS(th)}	V _{GS(th)} gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; \text{see } \frac{\text{Figure } 10}{10}$	2	3	4	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; \text{see } \frac{\text{Figure } 10}{10}$	-	-	4.4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; see Figure 10	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 10 V; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \ V; \ V_{GS} = -10 \ V; \ T_j = 25 \ ^{\circ}C$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 175 °C; see $\underline{Figure~11}$ and $\underline{12}$	-	-	60	mΩ
		V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; see Figure 11 and $\underline{12}$	-	26	30	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 44 V; V_{GS} = 10 V; see Figure 14	-	24	-	nC
Q _{GS}	gate-source charge			5	-	nC
Q _{GD}	gate-drain charge		-	9	-	nC
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; see <u>Figure 15</u>		864	1152	pF
C _{oss}	output capacitance			218	262	pF
C _{rss}	reverse transfer capacitance			139	191	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	14	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	68	-	ns
t _{d(off)}	turn-off delay time		-	83	-	ns
t _f	fall time		-	43	-	ns
L _D	internal drain inductance	measured from drain lead from package to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L _S	internal source inductance	measured from drain lead from package to source bond pad	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{100000000000000000000000000000000000$	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = -10 \text{ V};$	-	40	-	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	100	-	nC

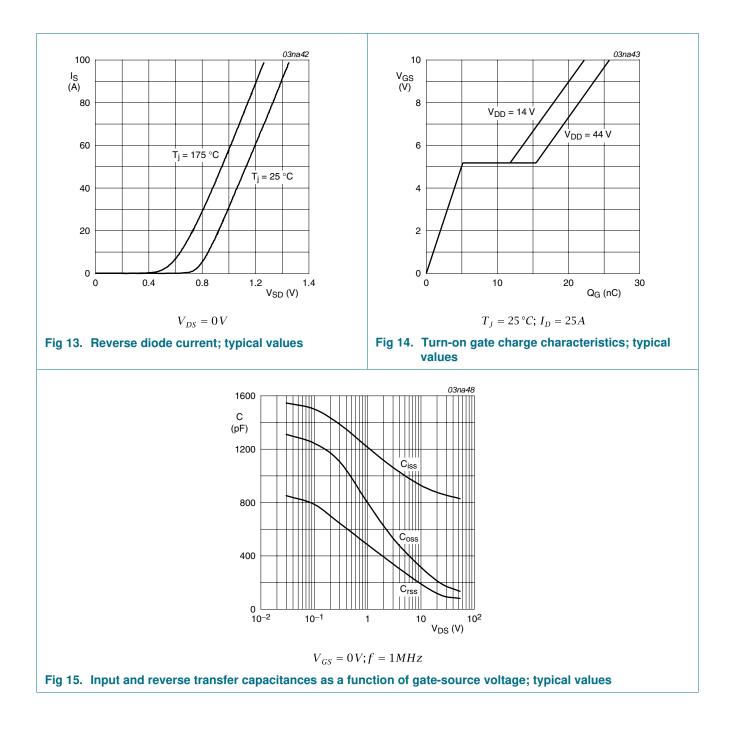
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BUK7230-55A



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7. Package outline

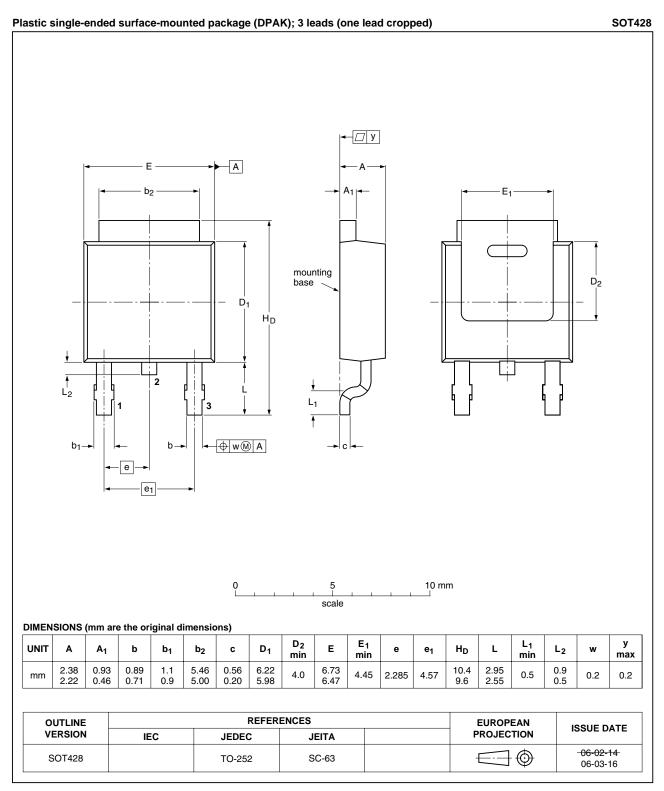


Fig 16. Package outline SOT428 (DPAK)

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BUK7230-55A_2

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8. Revision history

Table 7. Revision hi	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7230-55A_2	20100316	Product data sheet	-	BUK7230_55A-01
Modifications:	guidelines	of NXP Semiconductors	een redesigned to compl ne new company name v	
	· Leyal lexis	nave been adapted to th	le new company name w	mere appropriate.
BUK7230_55A-01	20000929	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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